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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number	10/761,918	
Sheet	1	of	1	Filing Date	01/20/2004
				First Named Inventor	Harry A. ATWATER et al.
				Group Art Unit	1764 (1765)
				Examiner Name	Unassigned Day-Ju Do
				Attorney Docket Number	047071-0107

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
jd	B1	5,013,681		GODBEY et al.	05-07-1991	
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Examiner Initials*	Cite No. ¹	U.S. Application Document	Name of Patentee or Applicant of Cited Document	Filing Date if Appropriate MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number			
jd	B22	10/784,586	ATWATER et al.	02/23/2004	
	B23	11/004,808	ATWATER et al.	12/07/2004	
jd	B24	11/004,948	ATWATER et al.	12/07/2004	

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	B25	JP	03-270220		FUJITSU LTD.	02-12-1991		Abst.

NON PATENT LITERATURE DOCUMENTS					
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jd	B26	WELDON et al., "Mechanism of Silicon Exfoliation Induced by Hydrogen/Helium Co-Implantation," Applied Physics Letters, Vol. 73, No. 25, December 21, 1998, pgs. 3721-3723.			

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INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

Date Submitted: 1/6/05

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Complete if Known

Application Number	10/761,918
Filing Date	01/20/2004
First Named Inventor	Harry A. ATWATER et al.
Group Art Unit	1764 <i>PH65</i>
Examiner Name	Unassigned <i>Dwy - Vu Dao</i>
Attorney Docket Number	047071-0107

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<i>JD</i>	A16	WO	01/03172			01/11/2001		

NON PATENT LITERATURE DOCUMENTS

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				Group Art Unit	1764
				Examiner Name	Unassigned
Sheet	2	of	7	Attorney Docket Number	047071-0107

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jd	A20	CHENG et al., Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates, IEEE Electron Device Letters, July 2001, pp. 321-323, Vol. 22, No. 7	
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		Examiner Name	Unassigned
Sheet 6 of 7	Attorney Docket Number	047071-0107	

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS								
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
90	A52	ZAHLER et al., Wafer Bonded Ge/Si Heterostructures for Photovoltaic Applications, (Abstract and Presentation), MRS 2002 Spring Meeting (04/2002)	
1	A53	ZAHLER J.M., Materials Integration by Wafer Bonding and Layer Transfer, (Presentation), 13 pages, MRS 2004 Spring Meeting (04/2004)	
	A54	ZAHLER et al., The Role of H in the H-Induced Exfoliation of GE Films, (Abstract and Presentation), MRS 2004 Spring Meeting, 16 pages (04/2004)	
	A55	ZAHLER et al., Wafer Bonded Expitaxial Templates for GaAs/Si Heterostructures, (Abstract and Presentation), MRS 2003 Spring Meeting, 16 pages, (04/2003)	
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	A57	ZAHLER et al., Wafer Bonding Processes for Ultrahigh Efficiency Photovoltaic Applications, (Abstract and Presentation), MRS 2001 Fall Meeting, (11/2001)	
	A58	ZAHLER et al., GE Layer Transfer to Si for Photovoltaic Applications, (Presentation), 14 pages, MRS 2001 Spring Conference, (04/2001)	
90	A59	ZAHLER et al., Wafer Bonding and Layer Transfer Processes for A 4-Junction Solar Cell, (Presentation) 29 th IEEE Photovoltaic Specialists Conference, New Orleans, USA, (05/2002)	

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		Application Number Filing Date First Named Inventor Group Art Unit Examiner Name Attorney Docket Number	10/761,918 01/20/2004 Harry A. ATWATER et al. 1764 Unassigned 047071-0107
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JD	A60	ZAHLE et al., Ge/Si Wafer Bonded Epitaxial Templates for GaAs/Si Heterostructures, (Abstract), MRS 2002 Fall Meeting, (11/2002)	
	A61	MORRAL et al., Bonding and Layer Transfer Process of InP on Silicon for the Elaboration of the Bottom Double Heterostructure of 4-Junction High Efficiency Solar Cells, (Abstract), MRS 2002 Fall Meeting, (11/2002)	
	A62	MORRAL et al., Assessment of Optical and Structural Properties of III-V Semiconductors Grown on InP/Si and Ge/Si Wafer Bonded Epitaxial Templates with Application to a Four-Junction Solar Cell, (Abstract), MRS 2003 Spring Meeting, (04/2003)	
	A63	MORRAL et al., Electrical and Structural Characterization of the Interface of Wafer Bonded InP/Si, MRS 2003 Spring Meeting, (04/2003)	
JD	A64	MORRAL et al., The Role of Hydrogen in H-Induced Exfoliation and Layer Transfer on InP, (Abstract), MRS 2004 Spring Meeting, (04/2004)	

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